

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

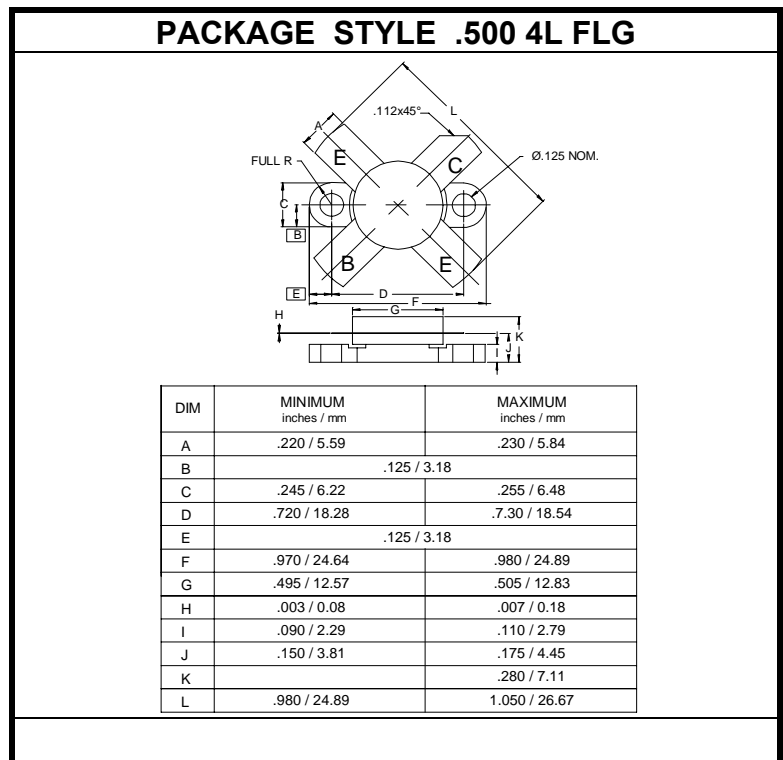
The **ASI 2SC2879** is a 12.5 V transistor designed primarily for SSB linear power amplifier applications up to 28 MHz.

FEATURES:

- $P_G = 13$ Typ. min. at 100 W/28 MHz
- $IMD_3 = -24$ dBc max. at 100 W_(PEP)
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	25 A
V_{CBO}	45 V
V_{CEO}	18 V
V_{EBO}	4.0 V
P_{DISS}	250 W @ $T_C = 25$ °C
T_J	-65 °C to +175 °C
T_{STG}	-65 °C to +175 °C
θ_{JC}	0.6 °C/W



CHARACTERISTICS $T_C = 25$ °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 100$ mA	45			V
BV_{CEO}	$I_C = 100$ mA	18			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
h_{FE}	$V_{CE} = 5.0$ V $I_C = 10$ A	10		150	---
C_{OB}	$V_{CB} = 12.5$ V $f = 1.0$ MHz		700		pF
G_P	$V_{CE} = 12.5$ V $I_{idle} = 100$ mA $f = 28$ MHz	13.0	15.2		dB
η_C	$P_{OUT} = 100$ W	35			%
IMD_3				-24	dBc
Z_{IN}	$V_{CC} = 12.5$ V $P_{OUT} = 100$ W $f = 28$ MHz	---	1.45 - j0.95	---	Ω
Z_{OUT}	$V_{CC} = 12.5$ V $P_{OUT} = 100$ W $f = 28$ MHz	---	1.45 - j1.0	---	Ω